



# PSMN038-100YL

N-channel 100 V 37.5 mΩ logic level MOSFET in LFPAK56

1 May 2013

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in LFPAK56 package. This product has been designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive
- LFPAK56 package is footprint compatible with other Power-SO8 types
- Qualified to 175 °C

## 3. Applications

- DC-to-DC converters
- Load switch
- TV power supplies

## 4. Quick reference data

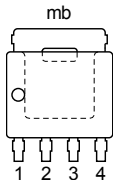
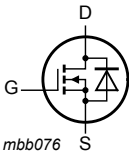
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	30	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	-	94.9	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 175\text{ °C}; \text{Fig. 13}; \text{Fig. 12}$	-	-	103.5	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}; \text{Fig. 12}$	-	30.2	37.5	mΩ
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{GS} = 5\text{ V}; I_D = 5\text{ A}; V_{DS} = 80\text{ V}; T_j = 25\text{ °C}; \text{Fig. 14}; \text{Fig. 15}$	-	21.6	-	nC
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; V_{DS} = 80\text{ V}; T_j = 25\text{ °C}; \text{Fig. 14}; \text{Fig. 15}$	-	8.3	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 30\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped; <a href="#">Fig. 3</a>	-	-	45.1	mJ

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LFAK56; Power-SO8 (SOT669)</b></p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN038-100YL	LFAK56; Power-SO8	Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN038-100YL	038100

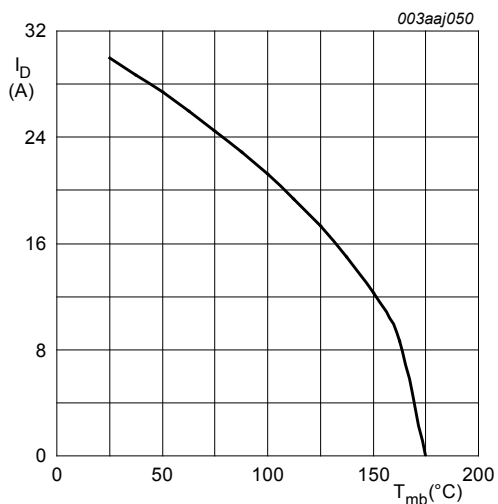
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

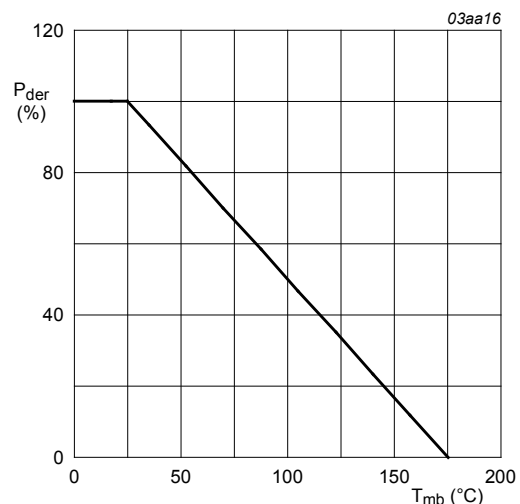
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$ ; $T_j \leq 175\text{ }^\circ\text{C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>	-	30	A

Symbol	Parameter	Conditions	Min	Max	Unit
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>	-	21.3	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a>	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	94.9	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	79	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	120	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 30\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; unclamped; <a href="#">Fig. 3</a>	-	45.1	mJ



**Fig. 1. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 10V$$



**Fig. 2. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

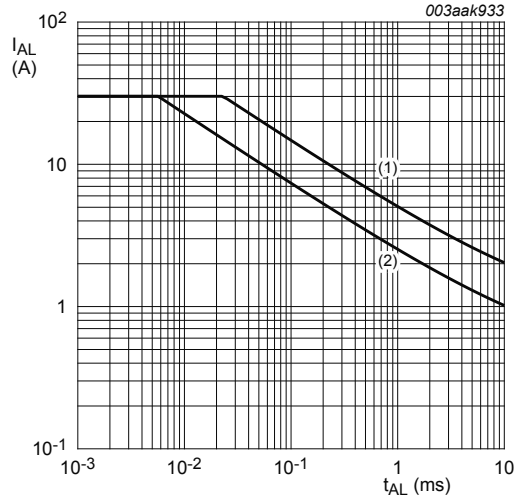


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j (init)} = 25^{\circ}C$ ; (2)  $T_{j (init)} = 100^{\circ}C$

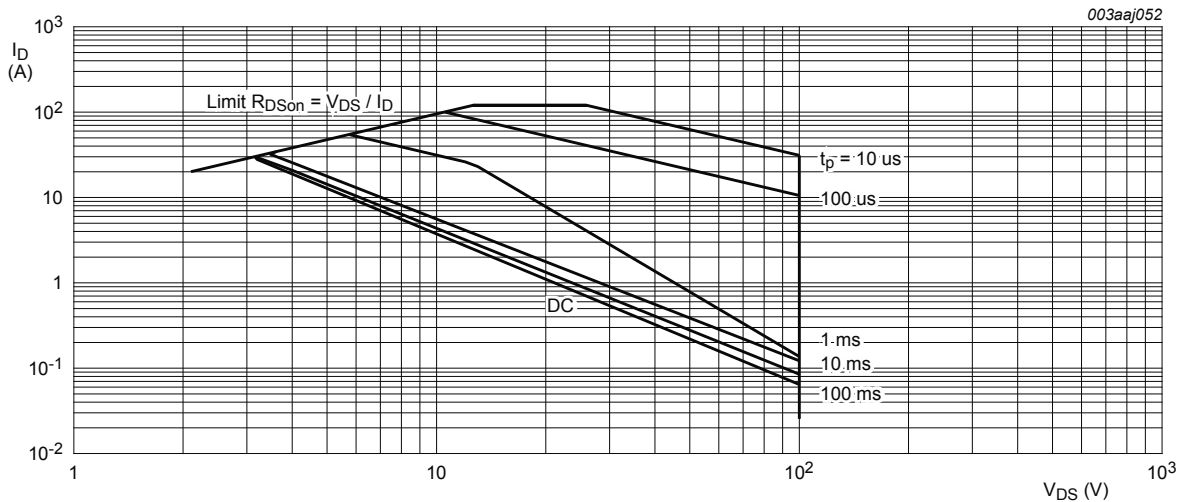


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	1.44	1.58	K/W

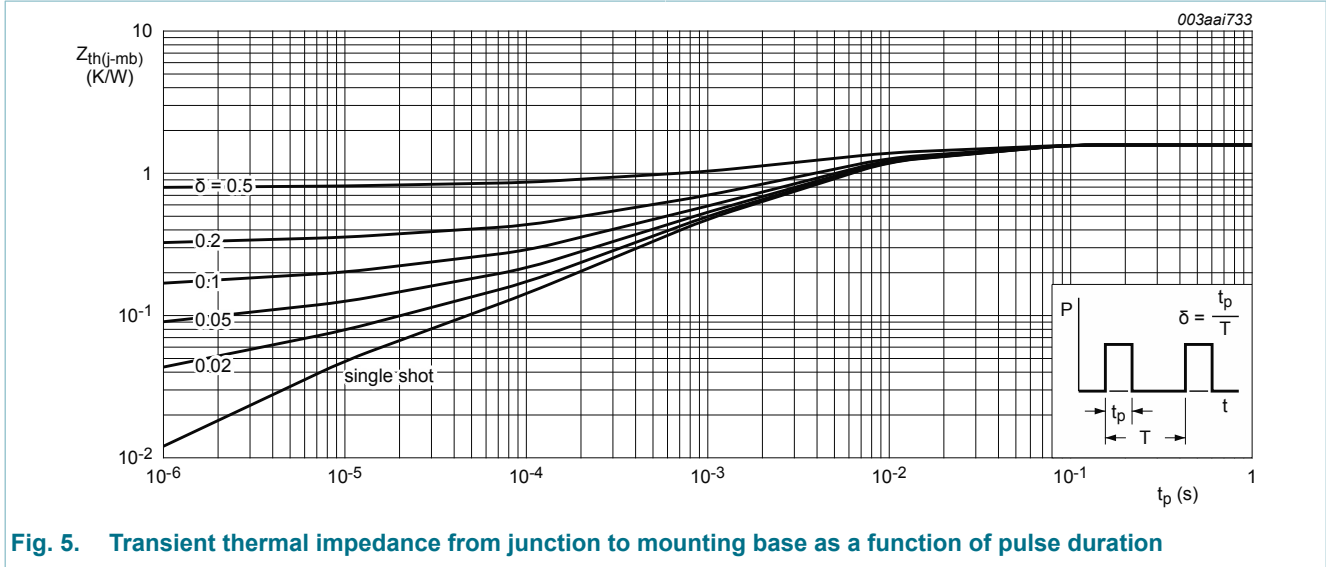


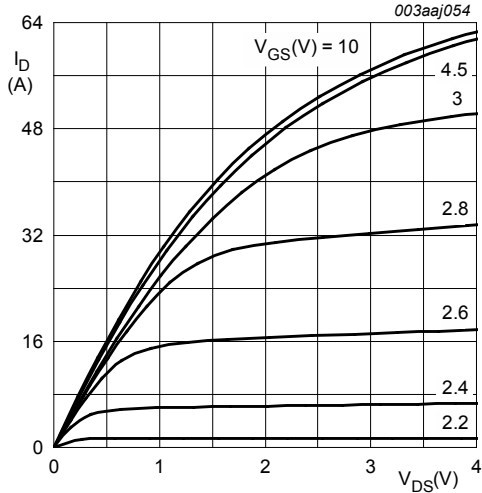
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

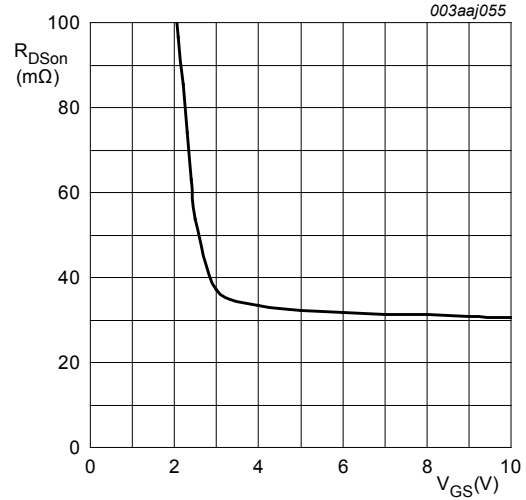
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	1	$\mu A$
		$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 5 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 12</a>	-	31.3	38	mΩ
		$V_{GS} = 10 V; I_D = 5 A; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 13</a> ; <a href="#">Fig. 12</a>	-	-	103.5	mΩ
		$V_{GS} = 10 V; I_D = 5 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 12</a>	-	30.2	37.5	mΩ
		$V_{GS} = 5 V; I_D = 5 A; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 13</a> ; <a href="#">Fig. 12</a>	-	-	105	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	1.64	-	Ω

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	39.2	-	nC
		I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	21.6	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	3.8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	8.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	2.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.1	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	2.3	-	V
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>	-	1905	-	pF
C <sub>oss</sub>	output capacitance		-	137	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	90	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 80 V; R <sub>L</sub> = 10 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	10	-	ns
t <sub>r</sub>	rise time		-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	31	-	ns
t <sub>f</sub>	fall time		-	18	-	ns
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a>	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 10 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	31	-	ns
Q <sub>r</sub>	recovered charge		-	44	-	nC



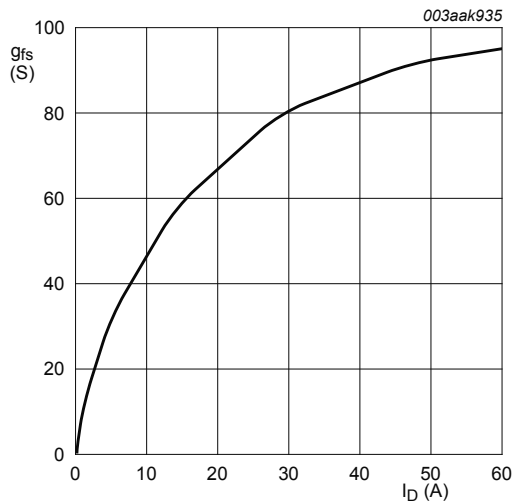
$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



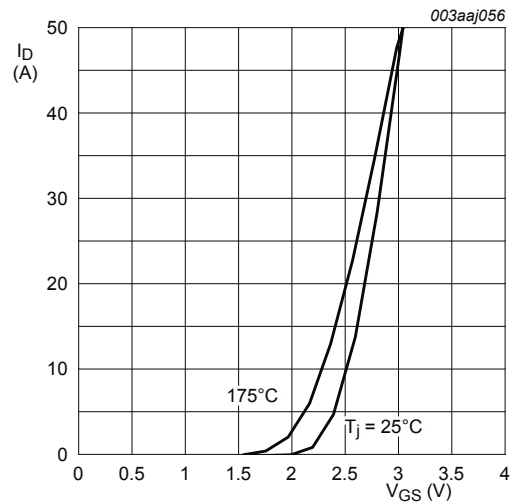
**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25^\circ\text{C}; I_D = 5\text{A}$



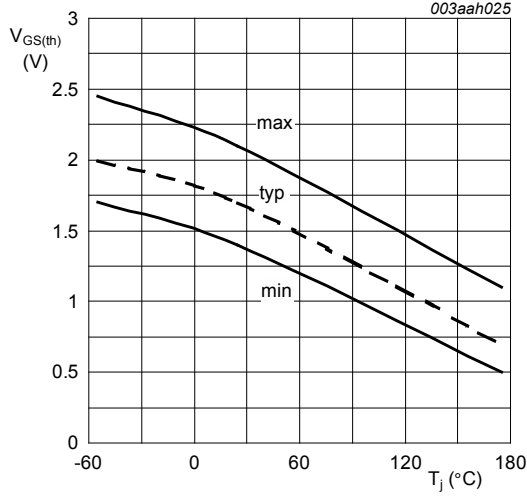
**Fig. 8. Forward transconductance as a function of drain current; typical values**

$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$



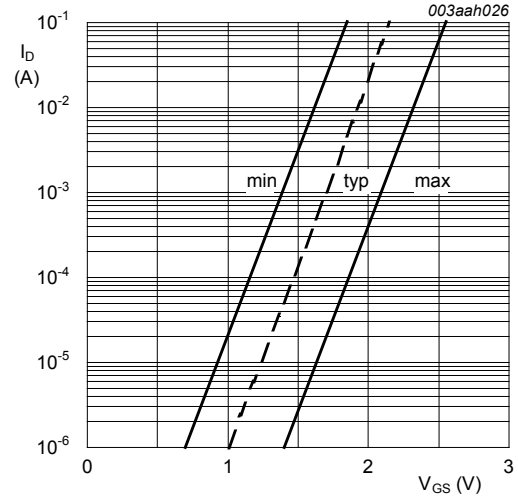
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

$V_{DS} = 10\text{V}$



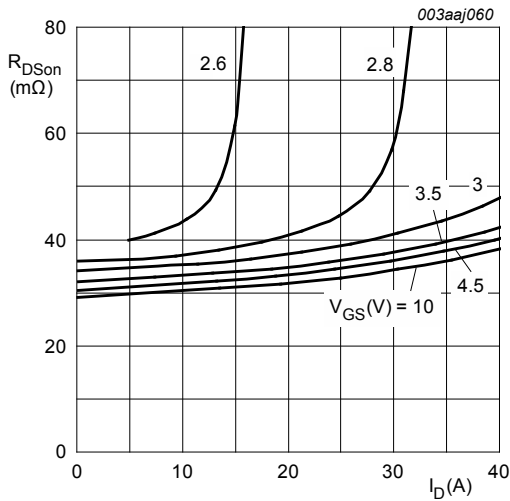
**Fig. 10. Gate-source threshold voltage as a function of junction temperature**

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$



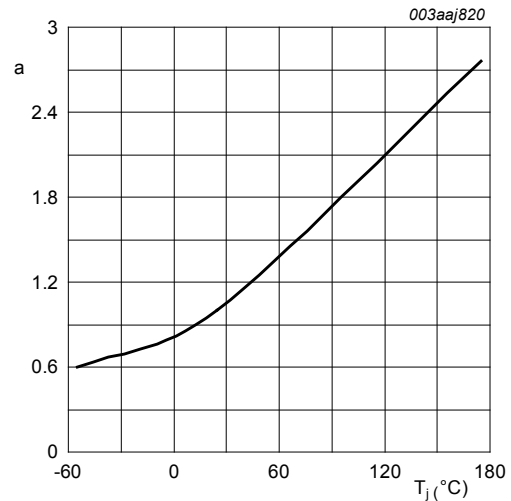
**Fig. 11. Sub-threshold drain current as a function of gate-source voltage**

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$



$$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$$

**Fig. 12. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$



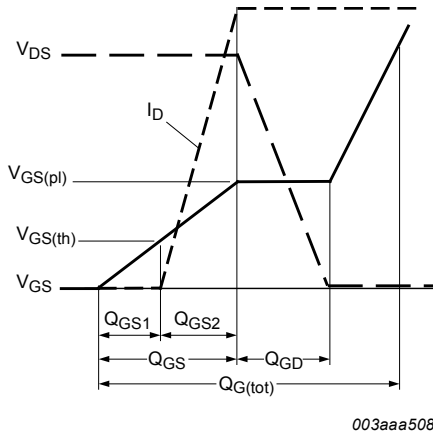


Fig. 14. Gate charge waveform definitions

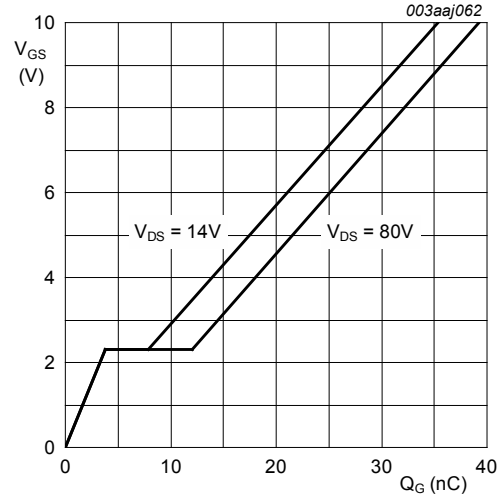


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 5\text{A}$

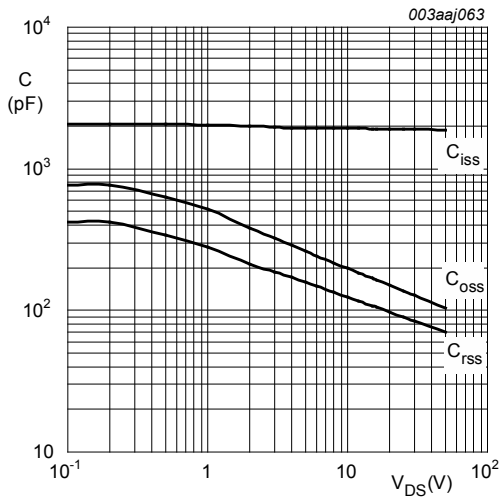


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{V}; f = 1\text{MHz}$

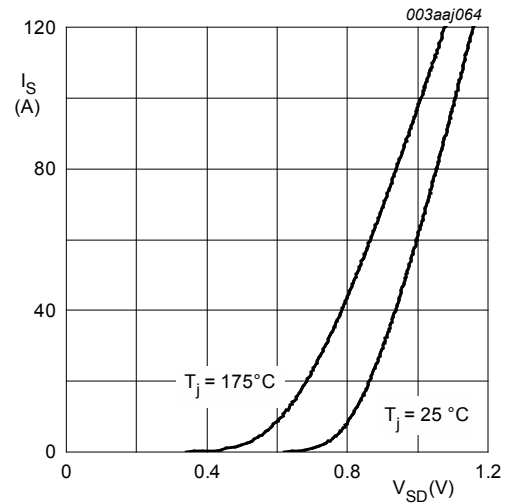


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0\text{V}$

### 11. Package outline

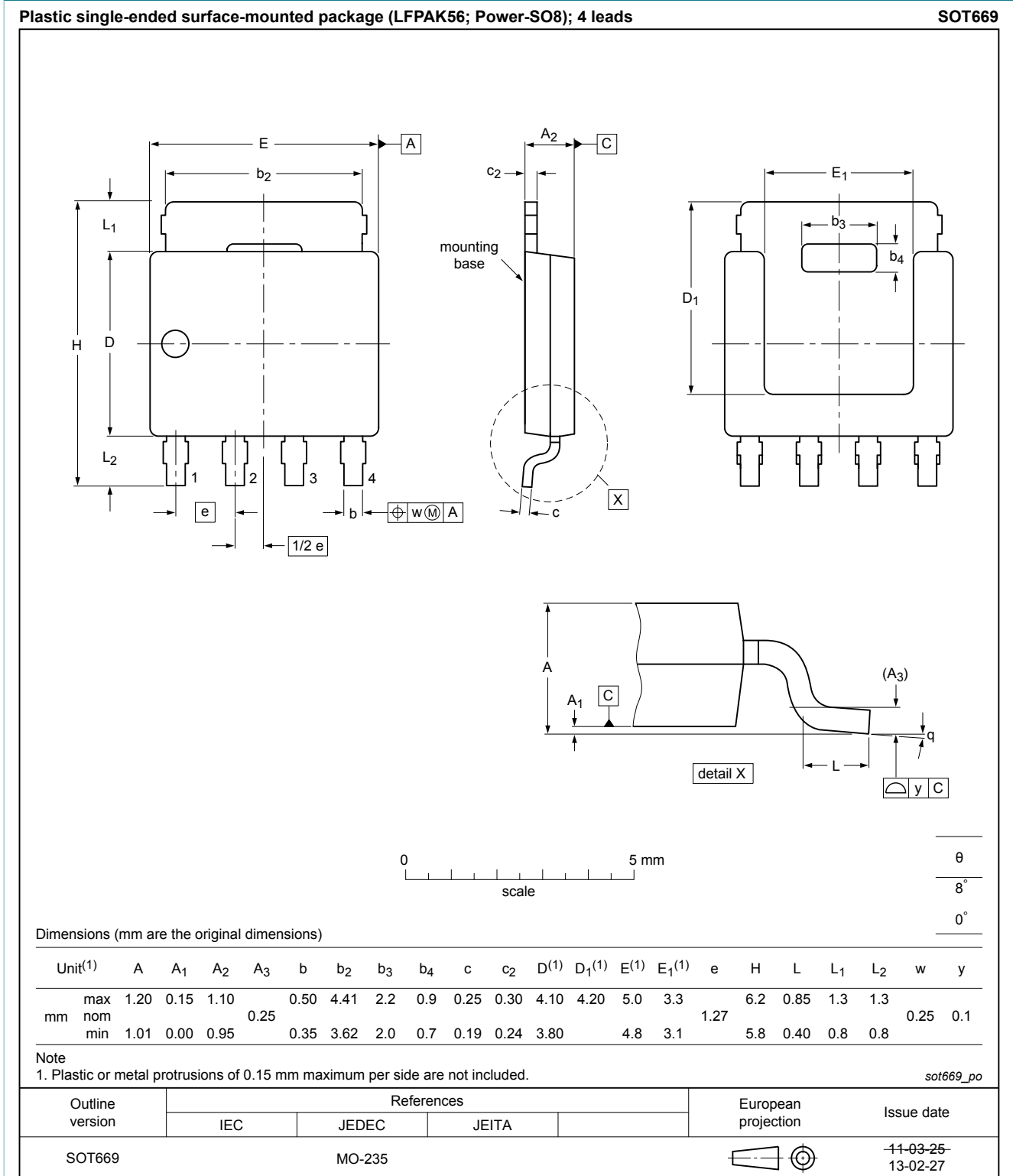


Fig. 18. Package outline LPAK56; Power-SO8 (SOT669)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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